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N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω) TYP.	I _D (A)	Q _g (TYP.)			
80	0.68 at V _{GS} = 10 V	400	193 nC			

TOLL Pin Configuration

N-Channel MOSFET

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS tested

APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	80	V			
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current (T, = 150 °C)	T _C = 25 °C		400	Α		
Continuous Drain Current (1) = 150 C)	T _C = 100 °C	l _D	335			
Pulsed Drain Current (t = 100 μs)	I _{DM}	I _{DM} 1600				
Avalanche Current	L = 0.1 mH	I _{AS}	385			
Single Avalanche Energy ^a	L=0.11IIII	E _{AS}	3180	mJ		
Maximum Dawar Discination 3	T _C = 25 °C	P _D	466 ^b	W		
Maximum Power Dissipation ^a	T _C = 100 °C	P _D	412 b			
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	LIMIT	UNIT				
Junction-to-Ambient (PCB Mount) ^c	t ≤ 10 s	R _{thJA}	9	°C/W			
Junction-to-Case (Drain)	Steady State	R _{thJC}	0.23	C/VV			

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

HALOGEN FREE

SPECIFICATIONS ($T_J = 25 ^{\circ}\text{C}$,					ı		
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}			-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.5	-	3.5		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85 ^{\circ}\text{C}$	-	-	30	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	400	-	-	Α	
Drain-Source On-State Resistance a	R-ac	$V_{GS} = 10 \text{ V}, I_D = 100 \text{ A}$	-	0.68	0.88	~ 0	
Diam-Source On-State Hesistance	R _{DS(on)}	V _{GS} = 6 V, I _D = 75 A	-	1.0	1.3	mΩ	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 100 A	-	275	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	20150	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 40 \text{ V}, f = 1 \text{ MHz}$	-	4995	-		
Reverse Transfer Capacitance	C _{rss}		-	108	-		
Total Gate Charge ^c	Q_g		-	193	-	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 100 \text{ A}$	-	62	-		
Gate-Drain Charge ^c	Q _{gd}		-	47	-		
Gate Resistance	R_g	f = 1 MHz	-	1.8	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	42	-		
Rise Time ^c	t _r	$V_{DD} = 40 \text{ V}, I_D = 100 \text{ A}, R_g = 6\Omega$	-	49	-	- ns	
Turn-Off Delay Time ^c	t _{d(off)}	$V_{GEN} = 10 \text{ V}$	-	77	-		
Fall Time ^c	t _f		-	36	-		
Drain-Source Body Diode Ratings and	Characteristi	ics ^b (T _C = 25 °C)					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	400	Α	
Pulsed Current (t = 100 μs)	I _{SM}		-	-	1600	Α	
Forward Voltage ^a	V_{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1	V	
Reverse Recovery Time	t _{rr}	1 100 4 100 47	-	186	-	ns	
Reverse Recovery Charge	Q _{rr}	$I_F = 100 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	505	_	nC	

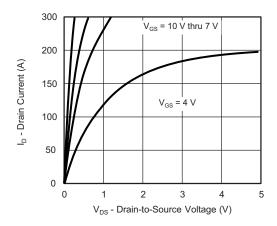
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

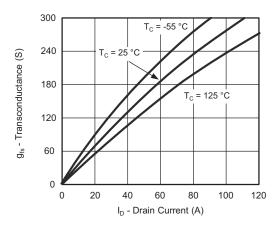
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



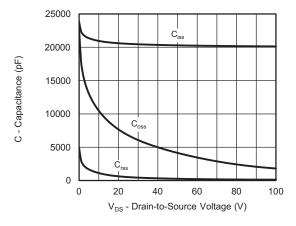
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



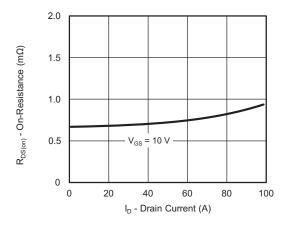
Output Characteristics



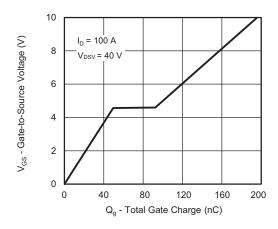
Transconductance



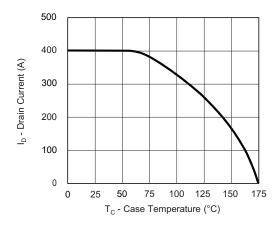
Capacitance



On-Resistance vs. Drain Current



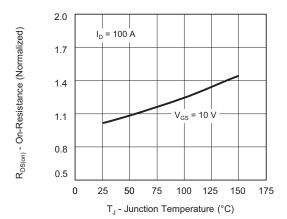
Gate Charge



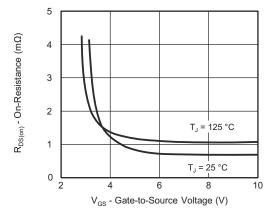
Current De-Rating



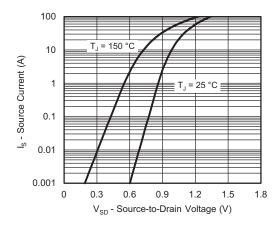
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



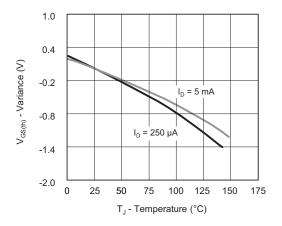
On-Resistance vs. Junction Temperature



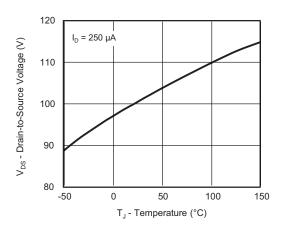
On-Resistance vs. Gate-to-Source Voltage



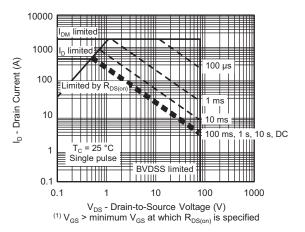
Source Drain Diode Forward Voltage



Threshold Voltage



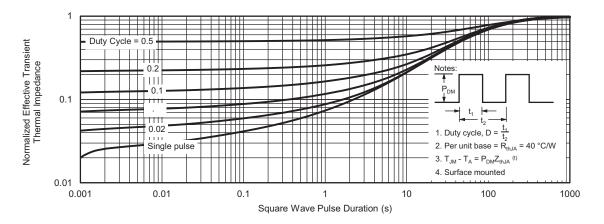
Drain Source Breakdown vs. Junction Temperature



Safe Operating Area



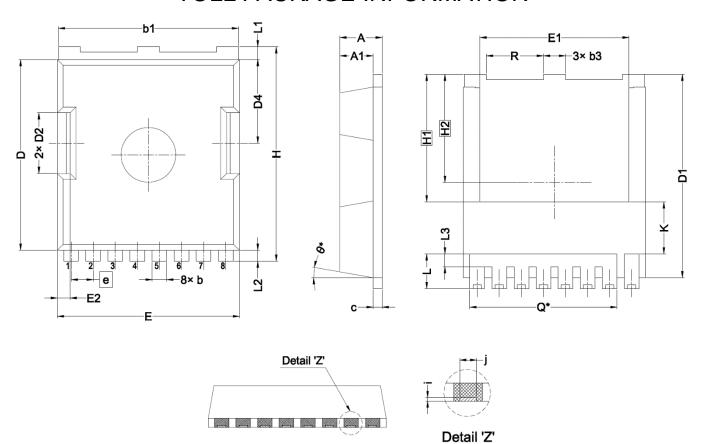
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



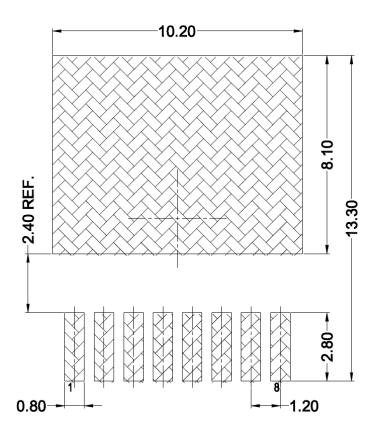
TOLL PACKAGE INFORMATION



CVMDOL		mm		SYMPOL mm			
SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
Α	2.20	2.30	2.40	Н	11.58	11.68	11.78
A 1	1.70	1.80	1.90	H1	6.95 BSC		
b	0.70	0.80	0.90	H2	5.89 BSC		
b1	9.70	9.80	9.90	i	0.10 REF		
b3	1.10	1.20	1.30	j	0.46 REF		
С	0.40	0.50	0.60	K	2.80 REF		
D	10.28	10.38	10.48	L	1.40	1.90	2.10
D1	10.98	11.08	11.18	L1	0.60	0.70	0.80
D2	3.20	3.30	3.40	L2	0.50	0.60	0.70
D4	4.45	4.55	4.65	L3	0.30	0.70	0.80
E	9.80	9.90	10.00	N	8		
E1	8.00	8.10	8.20	Q	8.00 REF		
E2	0.60	0.70	0.80	R	3.00	3.10	3.20
е	1.20 BSC		θ	10° REF			



TOLL RECOMMENDED LAND PATTERN



unit: mm





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